

Fig. 1

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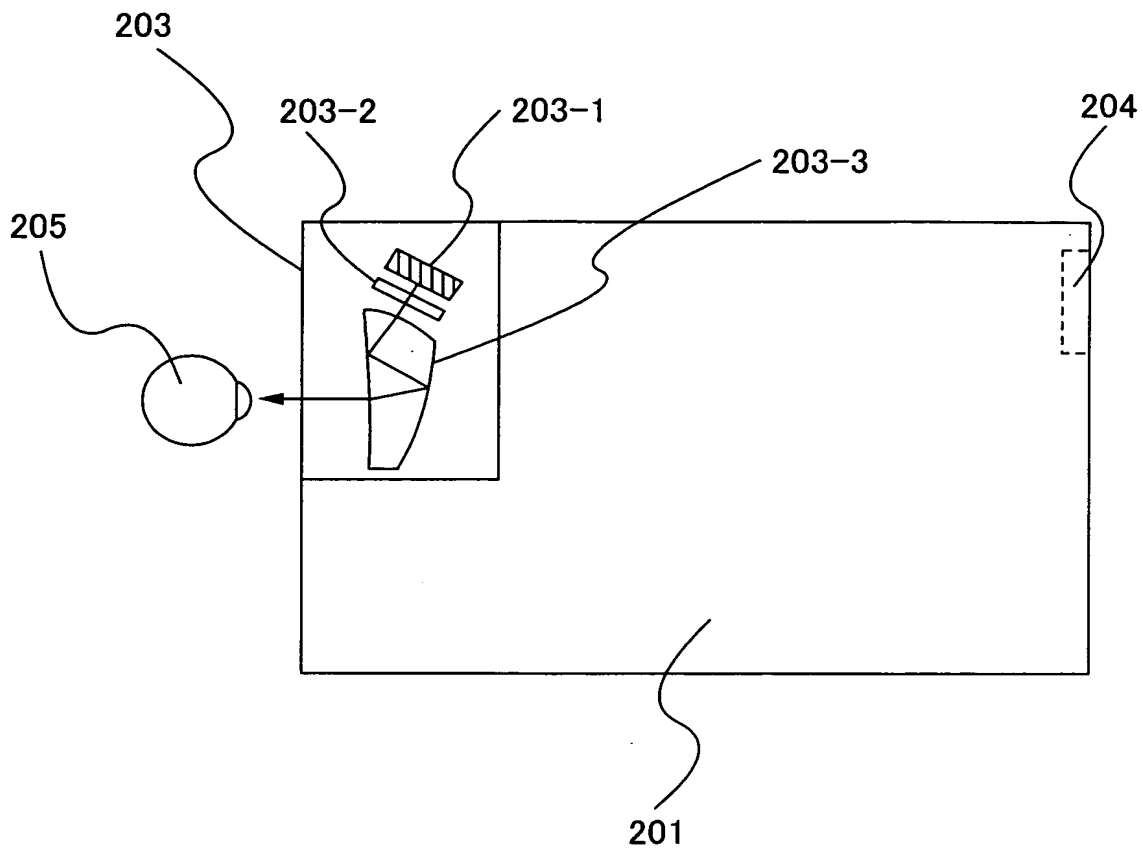


Fig. 2

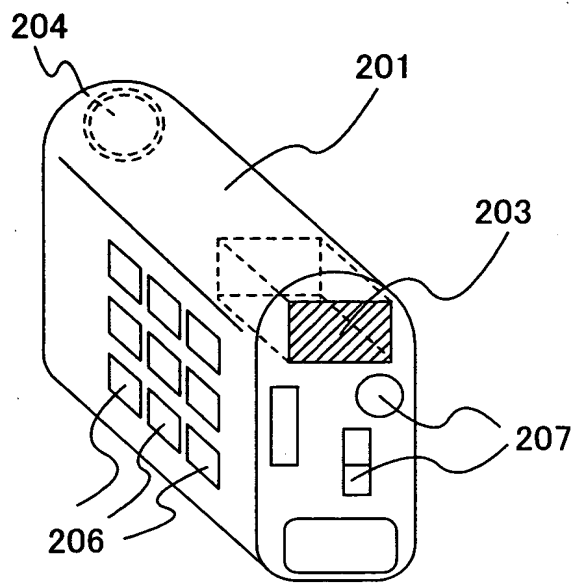


Fig. 3A

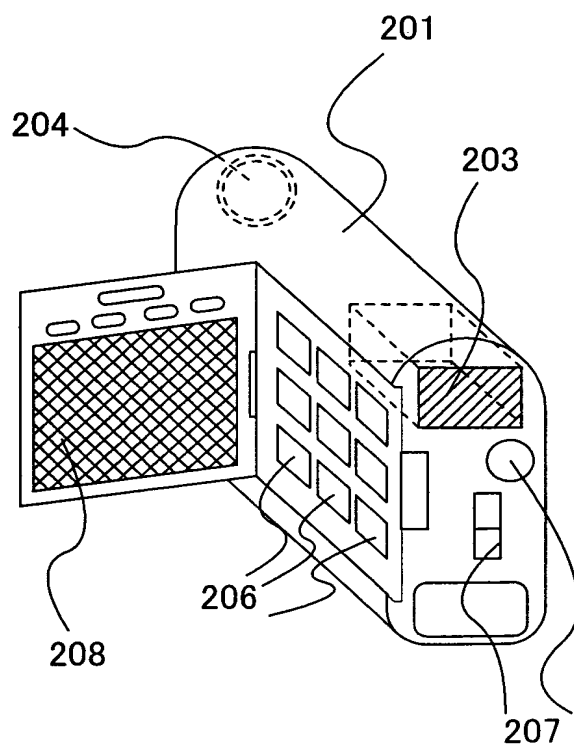


Fig. 3B

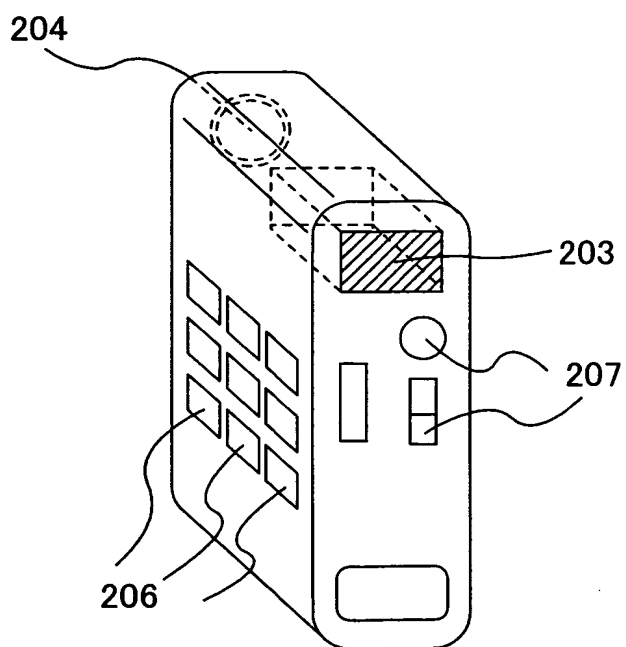


Fig. 3C

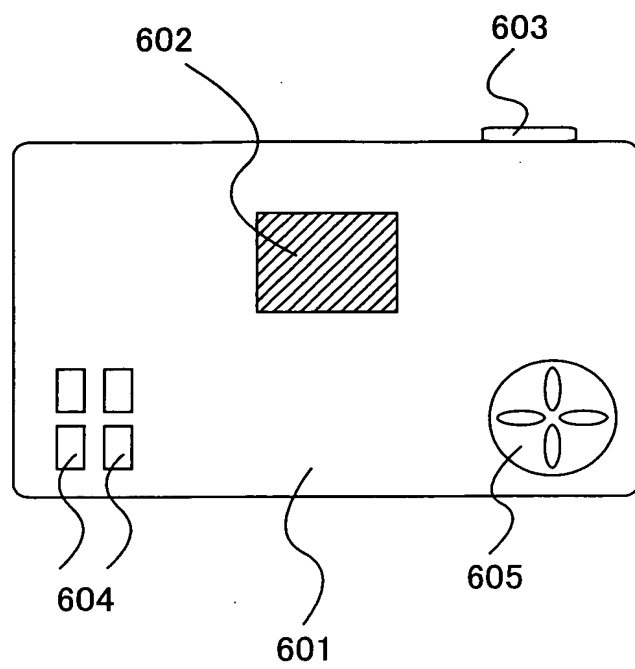


Fig. 6

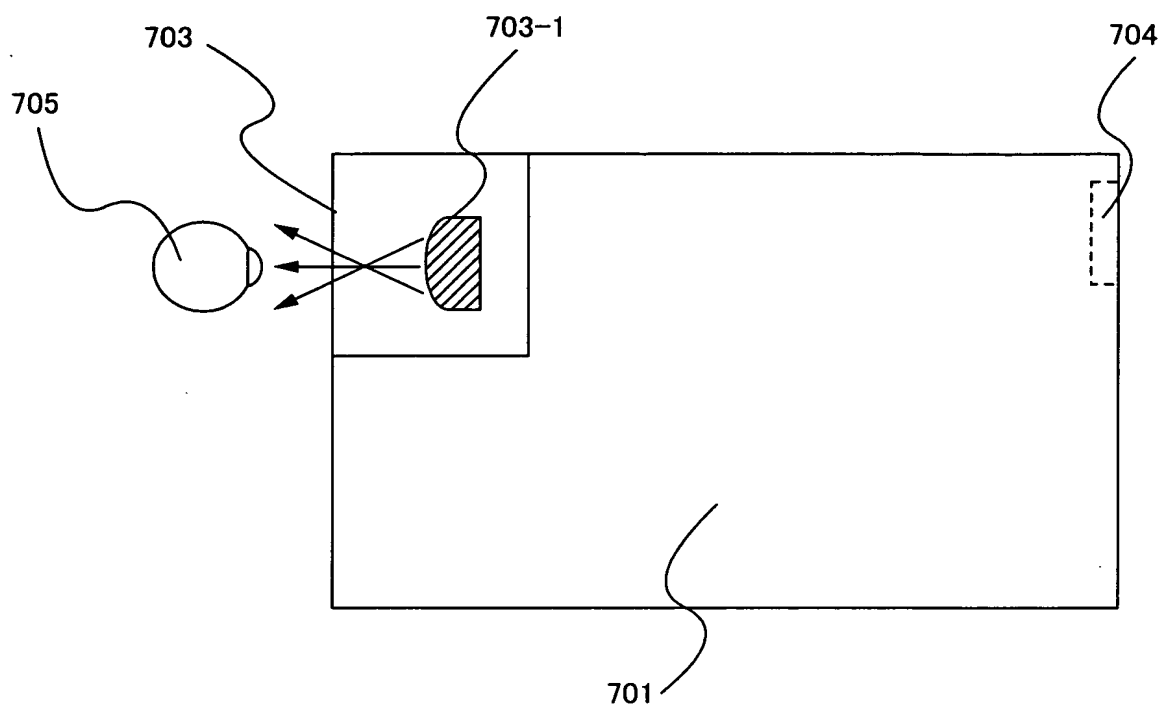


Fig. 7A

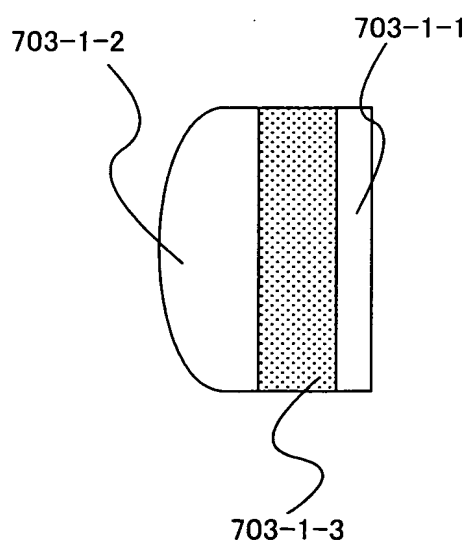


Fig. 7B

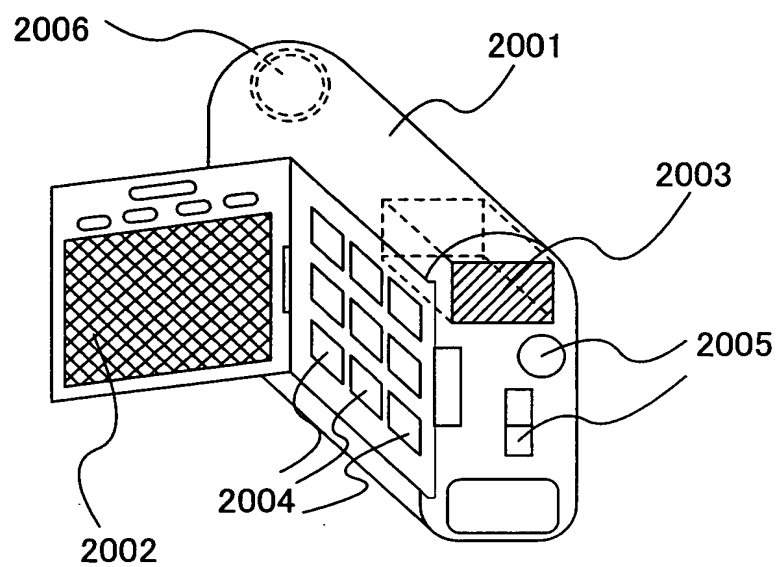


Fig. 8A (PRIOR ART)

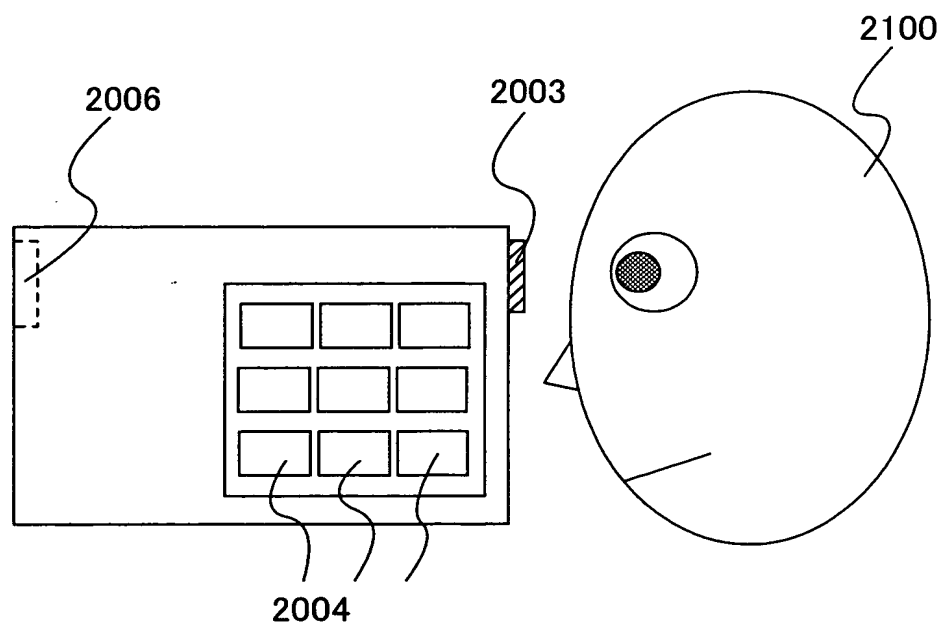


Fig. 8B (PRIOR ART)

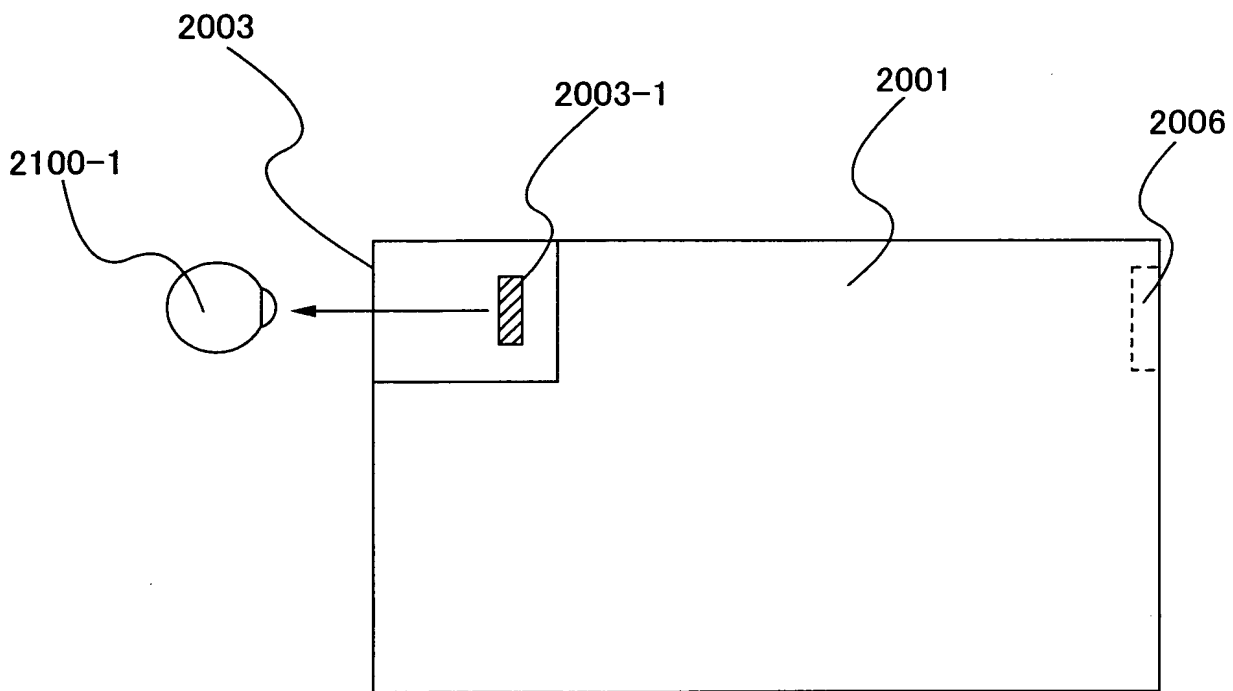


Fig. 9
(PRIOR ART)

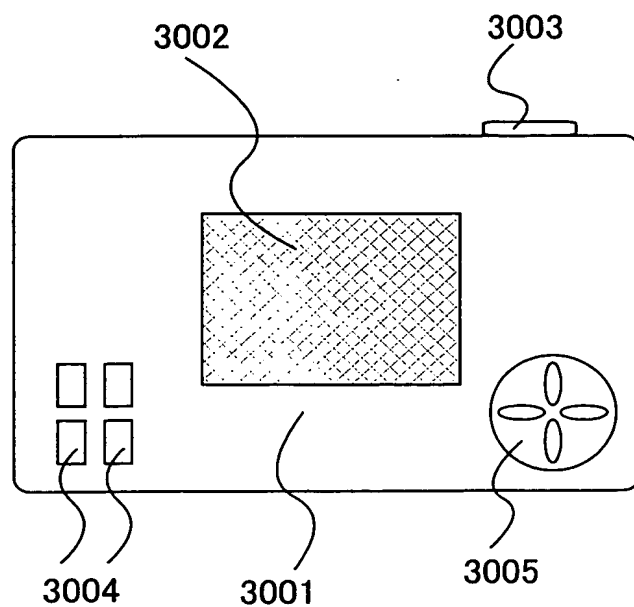


Fig. 10 (PRIOR ART)

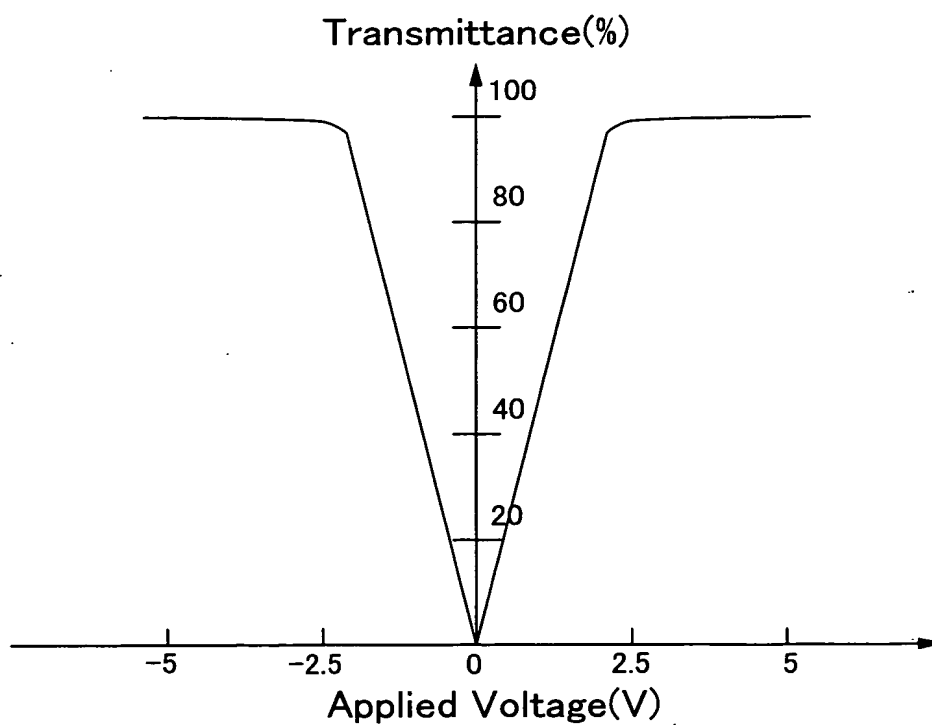
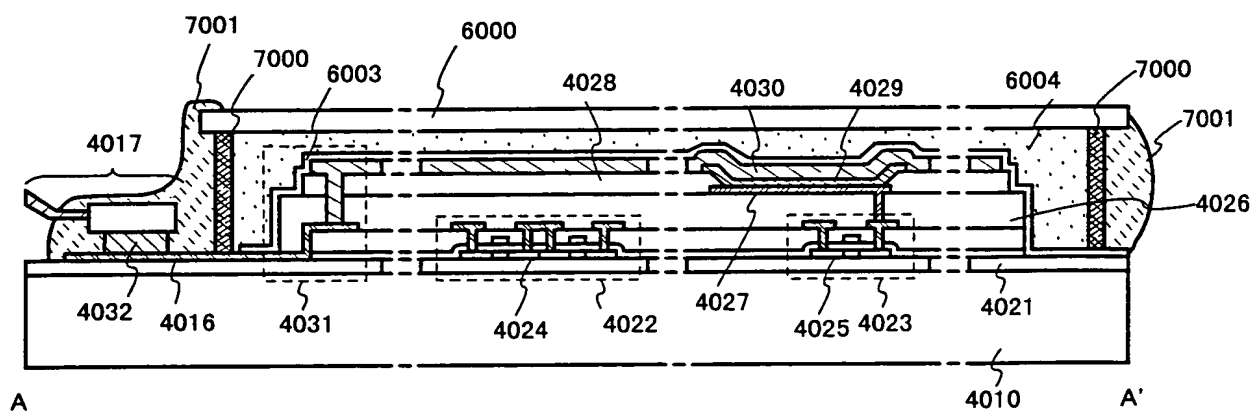
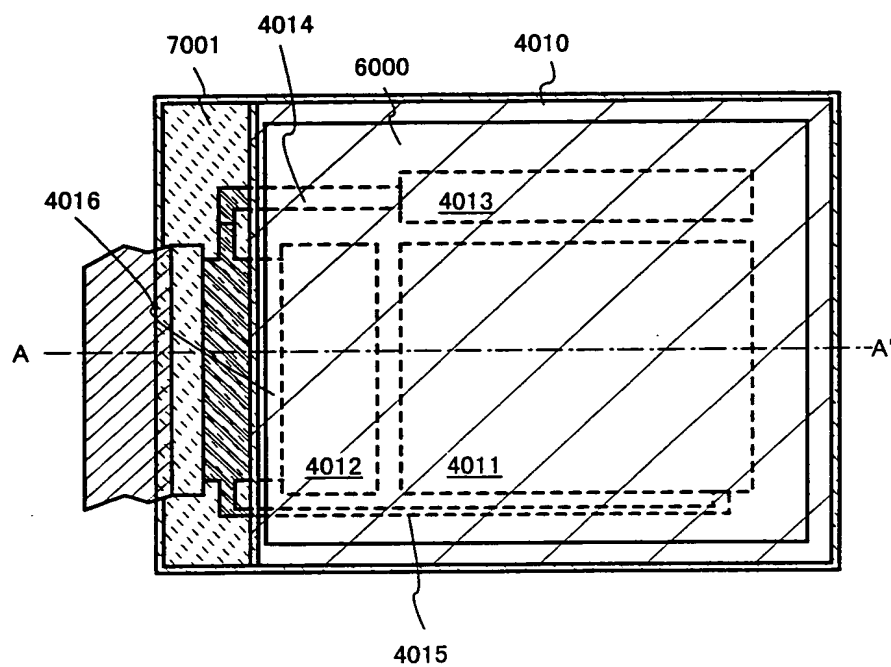


Fig. 11



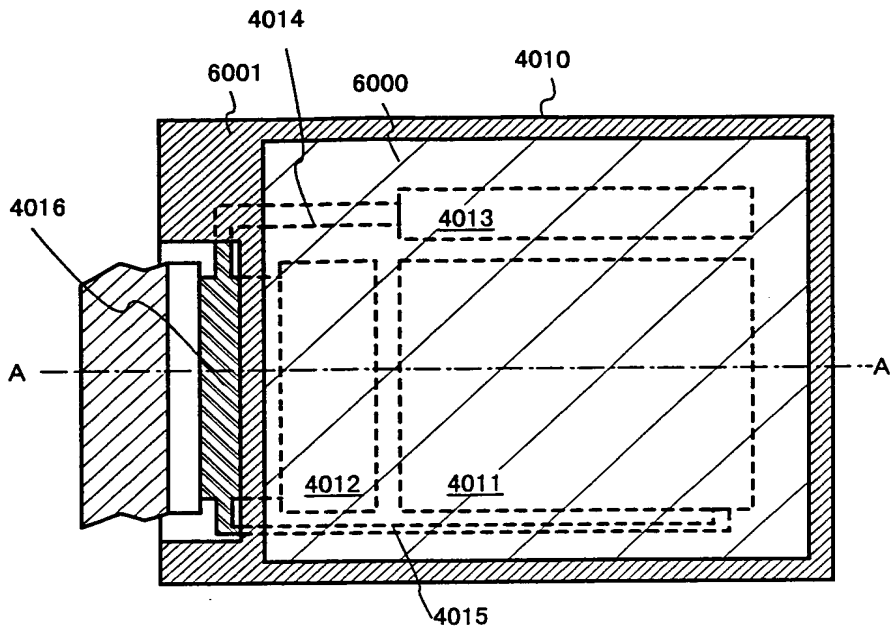


Fig. 13A

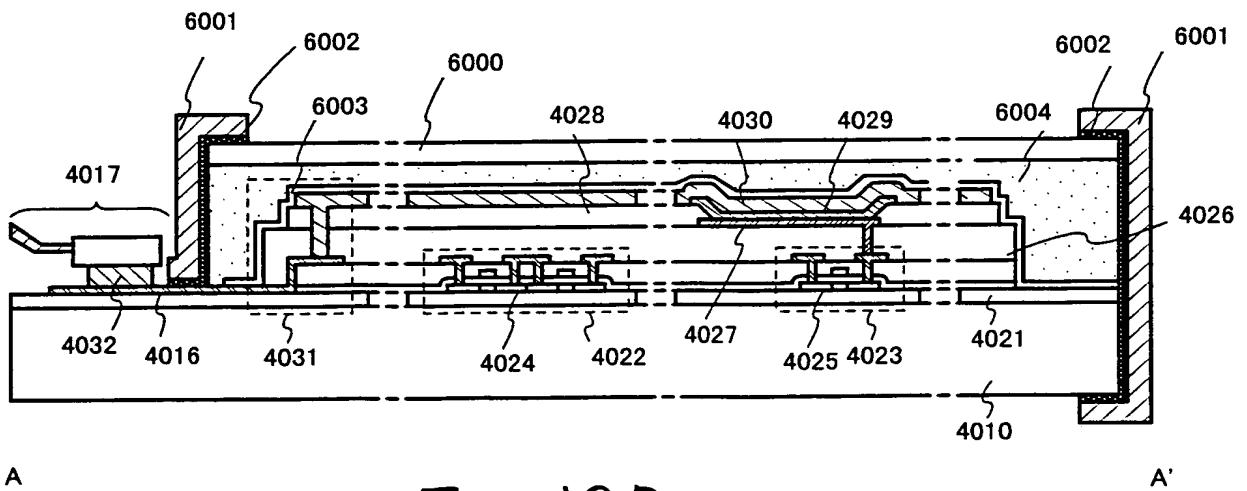


Fig. 13B

This cross-sectional view shows a semiconductor device with a central cavity 3043. The device is composed of several layers: a top layer 3040, a middle layer 3004, and a bottom layer 3035. The central cavity 3043 is defined by a bottom surface 3037 and side walls 3036. The side walls 3036 are formed by a series of rectangular blocks 3039a and 3039b. The top layer 3040 is formed by a series of rectangular blocks 3038. The middle layer 3004 is formed by a series of rectangular blocks 3037. The device is further defined by a top surface 3044a and a bottom surface 3044b. The central cavity 3043 is filled with a material 3043.

Fig. 15A

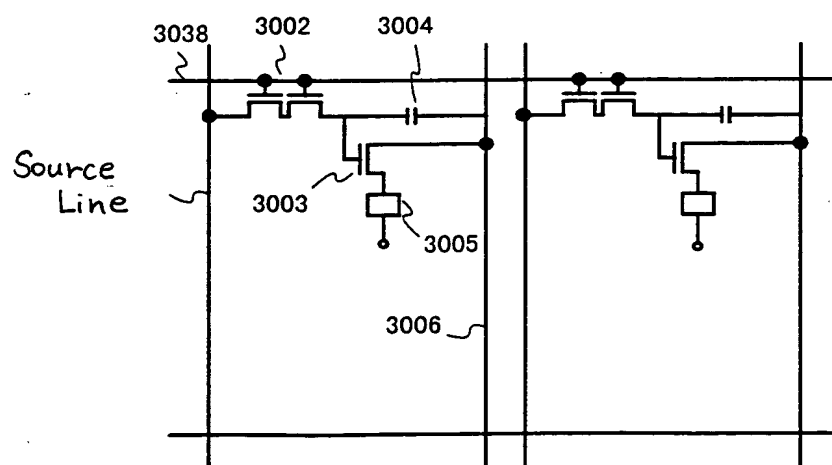


Fig. 15B

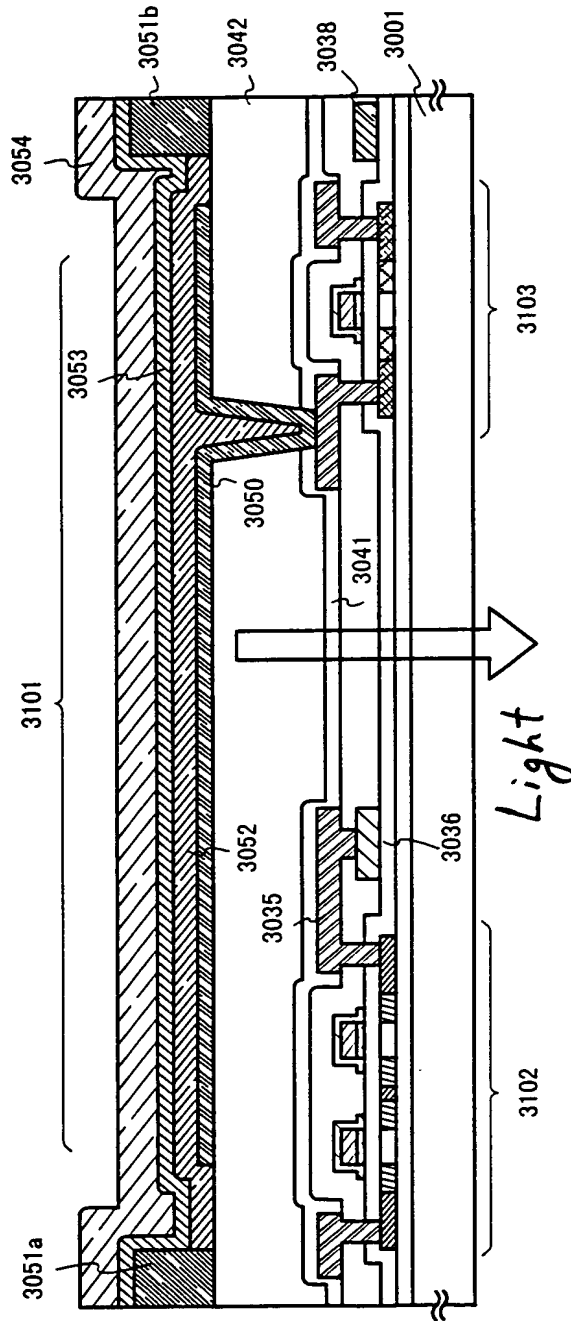


Fig. 16

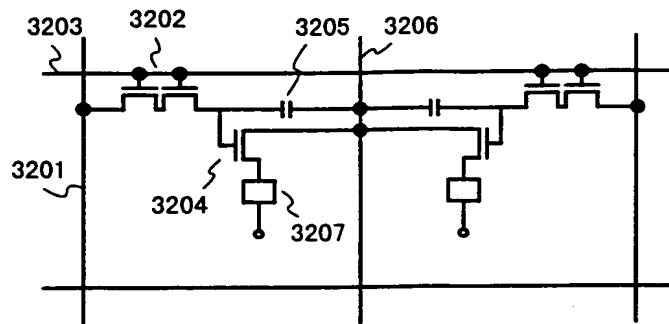


Fig. 17A

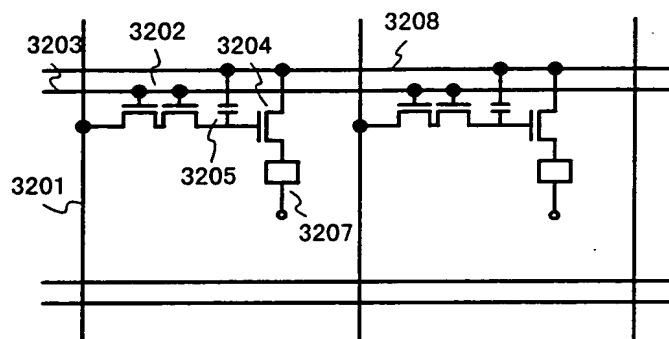


Fig. 17B

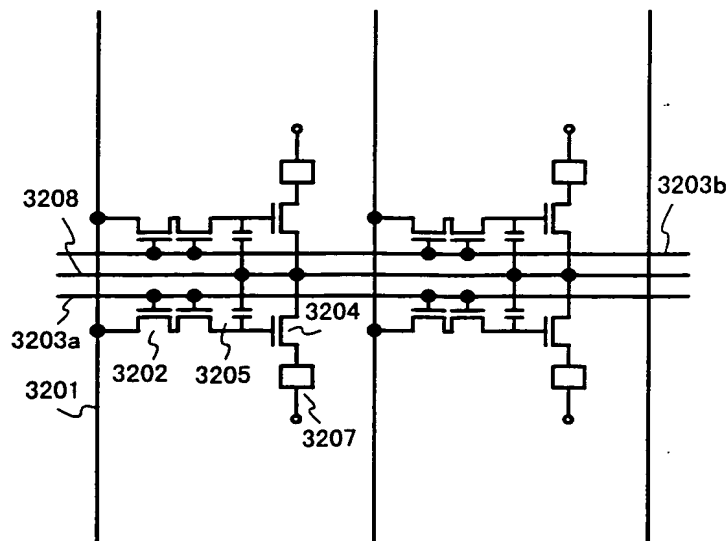


Fig. 17C